

**AMENDMENTS TO THE SPECIFICATION:**

Please add the following new paragraph after the paragraph ending on line 2 of Page 5:

-- Fig. 7 is a cross section view of an alternative substrate similar to the substrate shown in Fig. 2 expect for the presence of intermediate agent layer 100.--

Please replace the paragraph beginning at Page 5, line 9, with the following rewritten paragraph:

--The top surface of layer 40 shown in Fig. 1 is turned upside down and brought into intimate contact with surface 90 of substrate 80. The two surfaces 42 and 90 are brought together by the wafer bonding approach. The bonded surfaces of 42 and 90 are annealed at a temperature in the range from about 20°C to about 500°C for a time period in the range from about 2 hours to about 50 hours. Another embodiment, as shown in Fig. 7, uses at least one intermediate agent layer[[s]] 100 such as Ge, or metal materials which either have a low-melting point or react with silicon to form a silicide such materials may be tungsten (W), cobalt (Co), titanium (Ti) etc. to achieve high bonding strength at anneal temperatures in the range from 100° to 800°C. The anneal can be either a furnace anneal or a rapid thermal anneal (RTA).--